Name :	
Roll No. :	
Invigilator's Signature :	

CS/M.Tech (ECE)/SEM-2/MEC-204/2010 2010 ADVANCED EM THEORY & MICROWAVE

INTEGRATED CIRCUITS

*Time Allotted* : 3 Hours

Full Marks : 70

The figures in the margin indicate full marks.

Candidates are required to give their answers in their own words as far as practicable.

## **GROUP – A**

## (Very Short Answer Type Questions)

1. Answer any *five* of the following :

 $5 \times 2 = 10$ 

- i) State and explain the singularities of the vector field.
- ii) Given  $H = u_y x \cos \omega t$ , determine the current density  $J^t$ and hence total current flow  $i^t$  through a disk defined by z = 0,  $x^2 + y^2 = 1$ .
- iii) How to get right-handed circular polarized wave ?
- iv) Explain induction theorem and its importance.
- v) Define skin depth and explain its importance in shielding of electromagnetic waves.
- vi) Using neat diagram distinguish between Scattering and Diffraction.
- vii) Define Specific Absorption Rate (SAR) used in biological hazards of electromagnetic energies. Express it mathematically in terms of material parameters and electromagnetic field.

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 $4 \times 5 =$ 

20

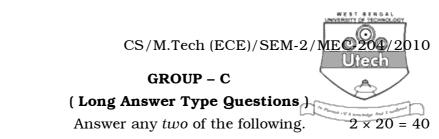
( Short Answer Type Questions)

**GROUP – B** 

Answer any four of the following.

- 2. From Maxwell's equations show that the power supplied by the sources within a region must equal that leaving the region plus that dissipated within the region plus the rate of increase in electric and magnetic energies stored within the region.
- 3. A micro strip line is composed of negligible Cu thickness on a substrate having  $\mathcal{E}_r = 8.4 \tan \delta = 0.0005$  and thickness 1 mm. If line width is 5 mm and operated at 10 GHz, calculate (a) the characteristic impedance, (b) the attenuation due to conductor and dielectric loss.
- 4. Describe the phenomenon of Rayleigh fading and Rician fading in wireless communication. Explain the methods of combating fading.
- 5. Find the impedances of two section quarter wave transformers to match a 50 ohm source and a 25 ohm load. Determine the VSWR at the input end of the first transformer and at the output end of the second transformer.
- 6. In a wireless communication link, fading margin = 30 dB, path loss = 100 dB, loss in the branching circuits of TX and RX = 10 dB, loss in the TX and RX antenna systems = 5 dB, TX antenna gain = 30 dB, and RX antenna gain = 40 dB. Calculate the overall system gain required.
- 7. Describe the construction and operation of reciprocal MIC phase shifter.

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8. a) State and prove the reciprocity theorem  $\langle a, b \rangle = \langle b, a \rangle$  10

b) Show that a current sheet  $J = \hat{u}_x J_o$  over the plane z = 0, produces the outward travelling plane waves expressed by

$$E_{x} = -(\eta J_{o} e^{-jkz})/2 \qquad z > 0$$
$$= -(\eta J_{o} e^{-jkz})/2 \qquad z < 0$$

in an infinite homogeneous medium.

10

- 9. a) Construct the possible solutions to Helmholtz equation in cylindrical coordinates and give the physical interpretation of each function. State where such functions are used. 10
  - b) (i) Prove that it is impossible to construct a perfectly matched, lossless, reciprocal three port passive device. 5
    - (ii) A matched micro strip isolator has insertion loss of 1 dB and isolation of 30 dB. Find the scattering parameters. 5
- 10. A GaAs MESFET amplifier is to be designed at 10 GHz with
  500 MHz bandwidth for maximum power gain. The measured
  parameters at 10 GHz with a 50 ohm reference are

Determine  $G_{A \max}$  and design input and output matching networks with a 50 ohm reference for maximum power gain.

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- 11. a) A shunt mounted PIN diode in a lossless 50 ohm strip line is represented by a shunt impedance Z = R + J X. The forward resistance of the diode is 0.1 ohm and the junction capacitance is 0.02 pF. Calculate the insertion loss and isolation at a frequency 2 GHz. 10
  - b) Design a Butterworth low-pass 50 ohm micro strip filter having cut-off frequency 2 GHz, and insertion loss of 30 dB at 4 GHz. Use lossless dielectric substrate of  $\varepsilon_r = 9.6$  and thickness = 0.635 mm. 10